

HAT2202C

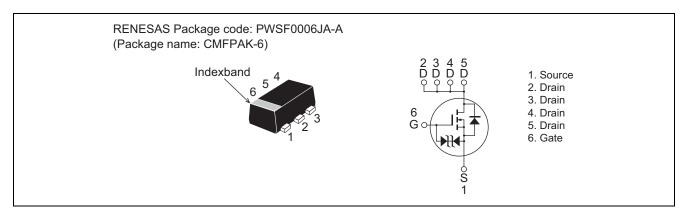
Silicon N Channel MOS FET Power Switching

REJ03G1236-0600 Rev.6.00 Oct 01, 2009

Features

- Low on-resistance $R_{DS(on)} = 31 \text{ m}\Omega \text{ typ. (at } V_{GS} = 4.5 \text{ V)}$
- Low drive current.
- High density mounting
- 2.5 V gate drive devices.

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	20	V
Gate to source voltage	V_{GSS}	±12	V
Drain current	I _D	3	A
Drain peak current	I _D (pulse) ^{Note1}	12	A
Body - Drain diode reverse drain current	I _{DR}	3	А
Channel dissipation	Pch ^{Note 2}	900	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. When using the glass epoxy board. (FR4 $40 \times 40 \times 1.6$ mm)

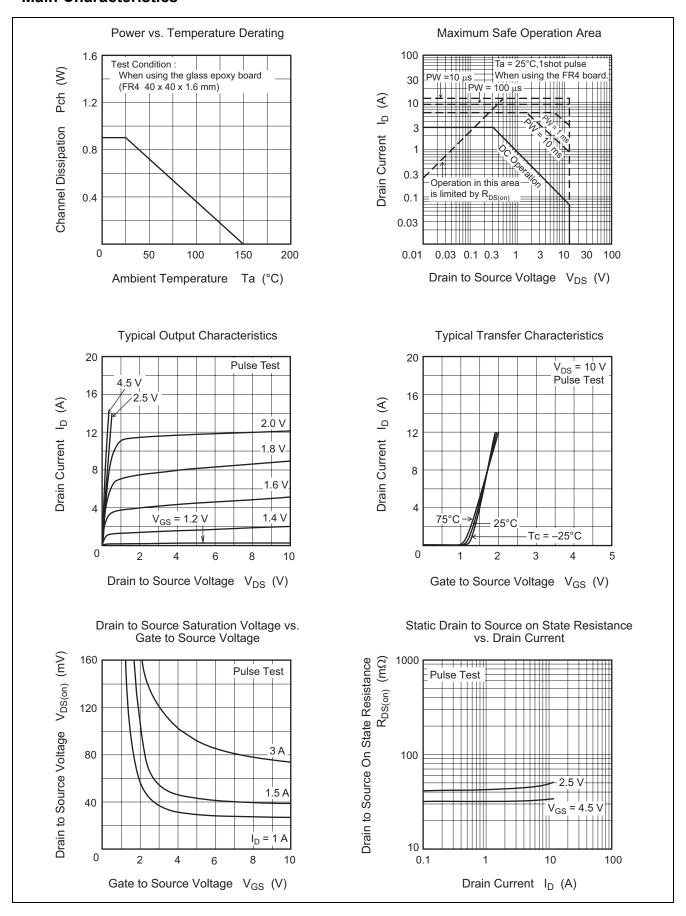
Electrical Characteristics

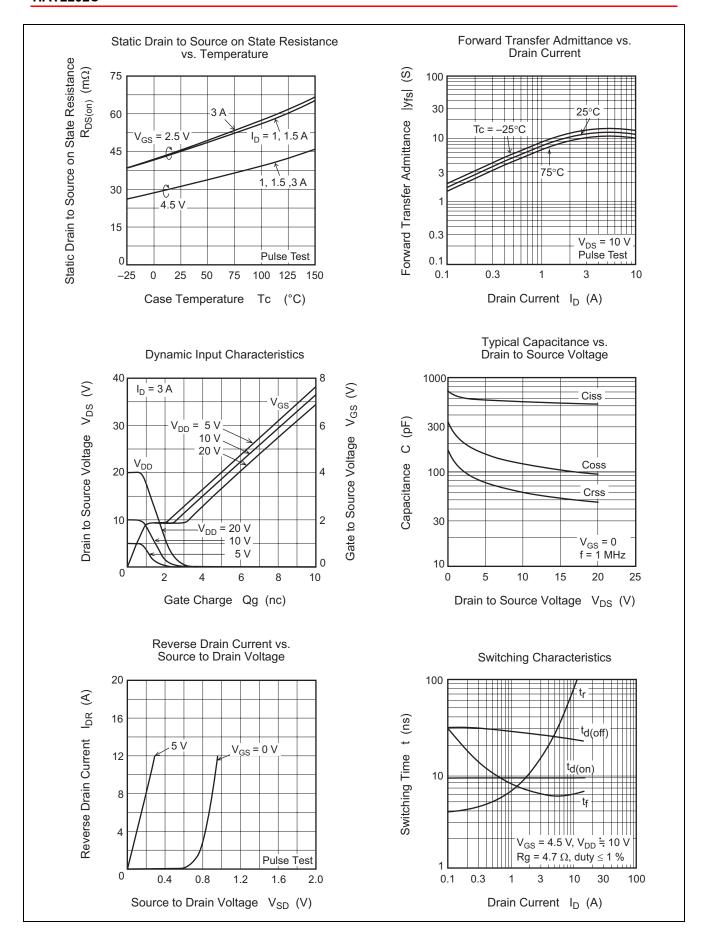
 $(Ta = 25^{\circ}C)$

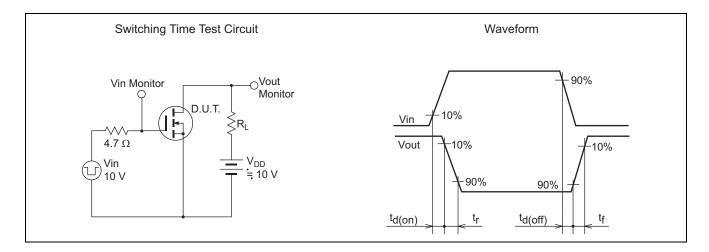
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	20	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to Source breakdown voltage	$V_{(BR)GSS}$	±12	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to Source leakage current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0$
Drain to Source leakage current	I _{DSS}	_	_	1	μΑ	V _{DS} = 20 V, V _{GS} = 0
Gate to Source cutoff voltage	$V_{GS(th)}$	0.4	_	1.4	V	I _D = 10 V, I _D = 1 mA
Drain to Source on state resistance	R _{DS(on)}	_	31	40	mΩ	$I_D = 1.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note3}}$
		_	43	55	mΩ	$I_D = 1.5 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y _{fs}	6.5	9.5	_	S	$I_D = 1.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	520	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	115	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	60	_	pF	
Total gate charge	Qg	_	6	_	nC	$V_{DD} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$
Gate to Source charge	Qgs	_	1	_	nC	I _D = 3 A
Gate to Drain charge	Qgd	_	1.4	_	nC	
Turn - on delay time	t _{d(on)}	_	9	_	ns	I _D = 1.5 A,
Rise time	t _r	_	8	_	ns	$V_{GS} = 10 \text{ V}, V_{DD} = 10 \text{ V},$
Turn - off delay time	$t_{d(off)}$	_	28	_	ns	$R_L = 6.7 \Omega, R_g = 4.7 \Omega$
Fall time	t _f	_	6	_	ns	
Body - Drain diode forward voltage	V_{DF}	_	0.8	1.1	V	$I_F = 3 \text{ A}, V_{GS} = 0^{\text{Note3}}$

Notes: 3. Pulse test

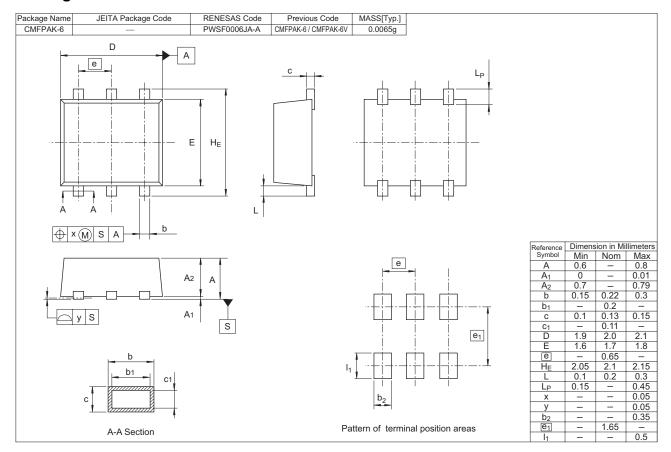
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2202C-EL-E	3000 pcs	Taping

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